

L Number	Hits	Search Text	DB	Time stamp
1	679	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist) and (photoresist with (reflow\$3 flow\$4))	USPAT; US-PGPUB	2001/12/13 11:54
2	22	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist) and (photoresist with (reflow\$3 flow\$4))	EPO; JPO; DERWENT; IBM TDB	2001/12/13 11:56
-	522159	substrate wafer semiconductor	USPAT; US-PGPUB	2001/12/11 17:11
-	49945	(substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist	USPAT; US-PGPUB	2001/12/11 17:11
-	17785	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist	USPAT; US-PGPUB	2001/12/11 17:11
-	1522	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist) and reflow\$3	USPAT; US-PGPUB	2001/12/11 16:36
-	155	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist) and reflow\$3) and tape	USPAT; US-PGPUB	2001/12/11 16:53
-	121	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist) and (photoresist with reflow\$3)	USPAT; US-PGPUB	2001/12/11 17:11
-	1598500	substrate wafer semiconductor	EPO; JPO; DERWENT; IBM TDB	2001/12/11 17:11
-	32212	(substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist	EPO; JPO; DERWENT; IBM TDB	2001/12/11 17:11
-	2389	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist	EPO; JPO; DERWENT; IBM TDB	2001/12/11 17:11
-	11	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist) and (photoresist with reflow\$3)	EPO; JPO; DERWENT; IBM TDB	2001/12/11 17:13
-	21	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4 ("Si.sib.3" adj "N.sub.4"))) and photoresist) and (photoresist with (reflow\$3 flow\$3))	EPO; JPO; DERWENT; IBM TDB	2001/12/11 17:13